

1214-150L

150 Watts, 36 Volts, 5 ms, 20% Radar 1200 to 1400 MHz

GENERAL DESCRIPTION

The 1214-150L is an internally matched, COMMON BASE transistor capable of providing 150 Watts of pulsed RF output power at 5 milliseconds pulse width, 20% duty factor across the band 1200 to 1400 MHz. This hermetically solder-sealed transistor is specifically designed for L-Band radar applications. It utilizes gold metallization and diffused emitter ballasting to provide high reliability and supreme ruggedness.

CASE OUTLINE 55ST-1

ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation

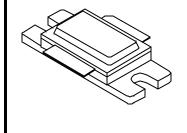
Device Dissipation @25°C¹ 320 W

Maximum Voltage and Current

 $\begin{array}{lll} \mbox{Collector to Base Voltage } (\mbox{BV}_{ces}) & 70 \ \mbox{V} \\ \mbox{Emitter to Base Voltage } (\mbox{BV}_{ebo}) & 3.5 \ \mbox{V} \\ \mbox{Collector Current } (\mbox{I}_c) & 15 \ \mbox{A} \\ \end{array}$

Maximum Temperatures

Storage Temperature -65 to +200 °COperating Junction Temperature +200 °C



ELECTRICAL CHARACTERISTICS @ 25°C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
P _{out}	Power Output	F = 1200-1400 MHz	140	150	200	W
P_{g}	Power Gain	Vcc = 36 Volts	7.15		8.7	dB
η_c	Collector Efficiency	Pin = 27 W Pulse Width = 5 mS Duty Factor = 20%	45			%
R_{L}	Return Loss		-9			dB
Pd	Pulse Droop				0.5	dB
VSWR ¹	Load Mismatch Tolerance	F=1200 MHz, Pin = 27W			3.0:1	

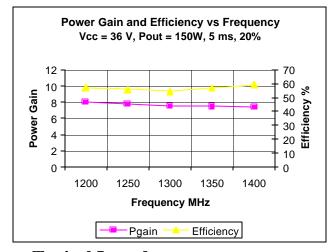
FUNCTIONAL CHARACTERISTICS @ 25°C

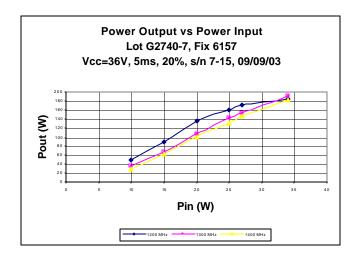
$\mathrm{BV}_{\mathrm{ebo}}$	Emitter to Base Breakdown	$I_e = 50 \text{ mA}$	3.0			V
BV_{ces}	Collector to Emitter Breakdown	$I_c = 100 \text{ mA}$	65			V
h_{FE}	DC – Current Gain	$V_{ce} = 5V, I_c = 1A$	20	55		
θjc ¹	Thermal Resistance				0.55	°C/W

NOTES: 1. Pulse condition of 5 mS, 20%

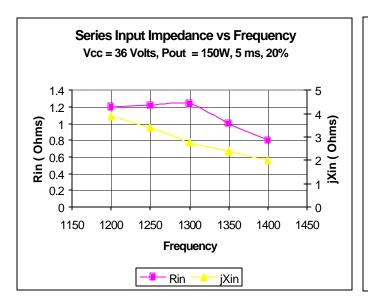
April 2005

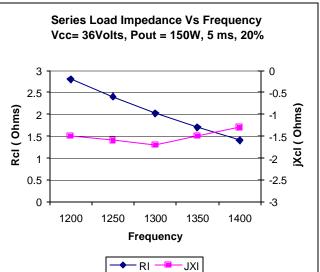
Performance Curves



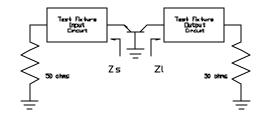


Typical Impedances

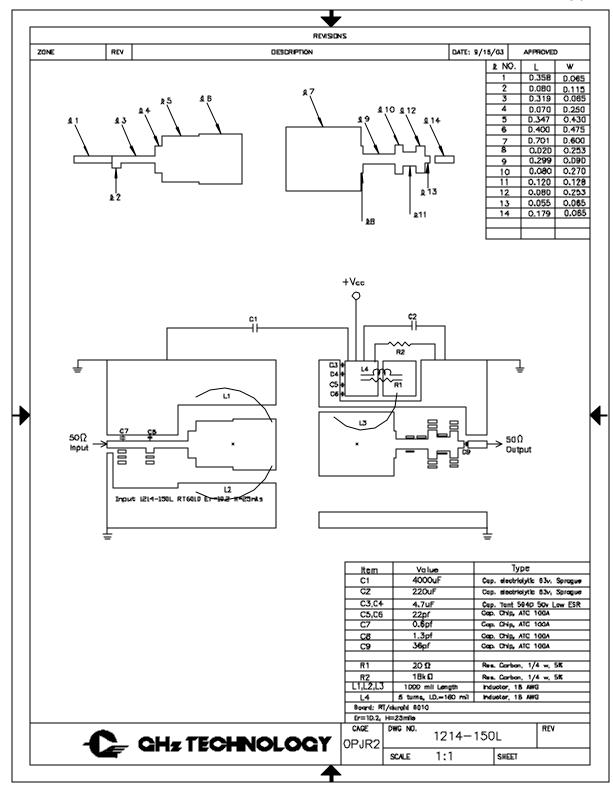




Impedanc						
е						
Freq	Zs	ZI				
1200	3.9-j1.2	2.8-j1.5				
1300	2.77-j1.24	2.02-j1.7				
1400	2.0-j0.8	2.02-j1.7				



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